IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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If you have any questions related to this document, please contact our nearest sales office via e-mail or phone (details via salesaddresses@ween-semi.com).

Thank you for your cooperation and understanding,

WeEn Semiconductors

founded by NXP

DATA SHEET

BYC10-600CT
Dual rectifier diode
ultrafast, low switching loss

Product specification

March 2001

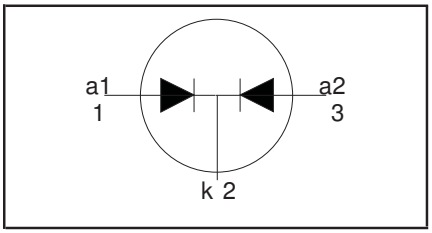
Rectifier diode ultrafast, low switching loss

BYC10-600CT

FEATURES

- Dual diode
- Extremely fast switching
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

SYMBOL



QUICK REFERENCE DATA

V_R = 600 V

$V_F \leq 1.75$ V

$I_{O(AV)}$ = 10 A

t_{rr} = 19 ns (typ)

APPLICATIONS

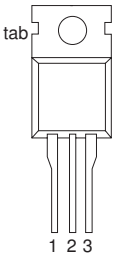
- Active power factor correction
- Half-bridge lighting ballasts
- Half-bridge/ full-bridge switched mode power supplies.

The BYC10-600CT is supplied in the SOT78 (TO220AB) conventional leaded package.

PINNING

PIN	DESCRIPTION
1	anode 1
2	cathode
3	anode 2
tab	cathode

SOT78 (TO220AB)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	Peak repetitive reverse voltage		-	600	V
V_{RWM}	Crest working reverse voltage		-	600	V
V_R	Continuous reverse voltage	$T_{mb} \leq 110$ ˚C	-	500	V
$I_{O(AV)}$	Average output current (both diodes conducting)	$\delta = 0.5$; with reapplied $V_{RRM(max)}$; $T_{mb} \leq 50$ ˚C[1]	-	10	A
I_{FRM}	Repetitive peak forward current per diode	$\delta = 0.5$; with reapplied $V_{RRM(max)}$; $T_{mb} \leq 50$ ˚C[1]	-	10	A
I_{FSM}	Non-repetitive peak forward current per diode	t = 10 ms	-	40	A
		t = 8.3 ms sinusoidal; $T_j = 150$˚C prior to surge with reapplied $V_{RWM(max)}$	-	44	A
T_{stg}	Storage temperature		-40	150	˚C
T_j	Operating junction temperature		-	150	˚C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base	per diode	-	-	2.5	K/W
		both diodes	-	-	2.2	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	in free air.	-	60	-	K/W

1 $T_{mb(max)}$ limited by thermal runaway

ELECTRICAL CHARACTERISTICS

T_j = 25 ˚C, per diode unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	Forward voltage	I_F = 5 A; T_j = 150˚C	-	1.4	1.75	V
		I_F = 10 A; T_j = 150˚C	-	1.75	2.2	V
		I_F = 5 A;	-	2.0	2.9	V
I_R	Reverse current	V_R = 600 V	-	9	100	µA
		V_R = 500 V; T_j = 100 ˚C	-	0.9	3.0	mA
t_{rr}	Reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 50 A/µs	-	30	50	ns
t_{rr}	Reverse recovery time	I_F = 5 A; V_R = 400 V; dI_F/dt = 500 A/µs	-	19	-	ns
t_{rr}	Reverse recovery time	I_F = 5 A; V_R = 400 V; dI_F/dt = 500 A/µs; T_j = 100˚C	-	25	30	ns
I_{rrm}	Peak reverse recovery current	I_F = 5 A; V_R = 400 V; dI_F/dt = 50 A/µs; T_j = 125˚C	-	0.7	3	A
I_{rrm}	Peak reverse recovery current	I_F = 5 A; V_R = 400 V; dI_F/dt = 500 A/µs; T_j = 125˚C	-	8	11	A
V_{fr}	Forward recovery voltage	I_F = 10 A; dI_F/dt = 100 A/µs	-	9	11	V

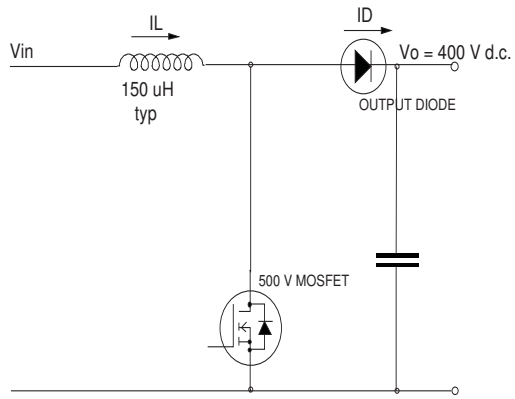


Fig.1. Typical application, output rectifier in boost converter power factor correction circuit. Continuous conduction mode, where the transistor turns on whilst forward current is still flowing in the diode.

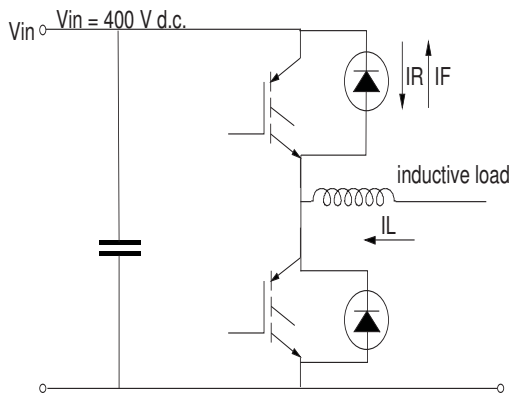


Fig.2. Typical application, freewheeling diode in half bridge converter. Continuous conduction mode, where each transistor turns on whilst forward current is still flowing in the other bridge leg diode.

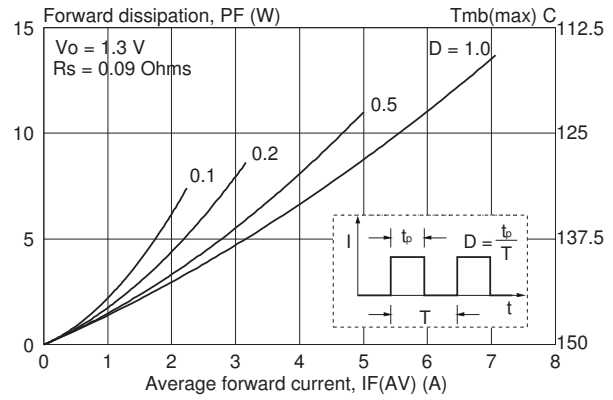


Fig.3. Maximum forward dissipation per diode as a function of average forward current; rectangular current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

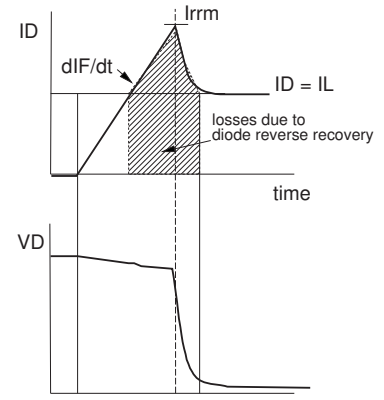


Fig.6. Origin of switching losses in transistor due to diode reverse recovery.

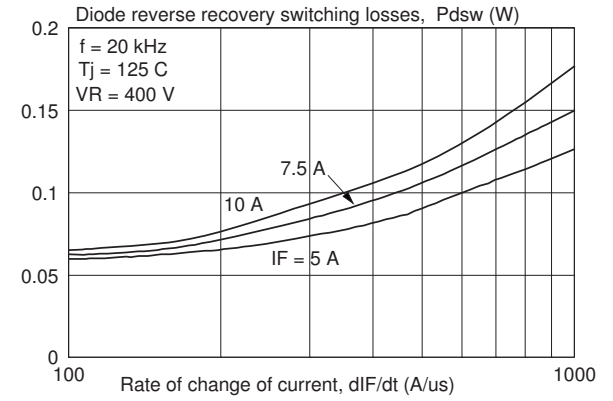


Fig.4. Typical reverse recovery switching losses per diode, as a function of rate of change of current dI_F/dt.

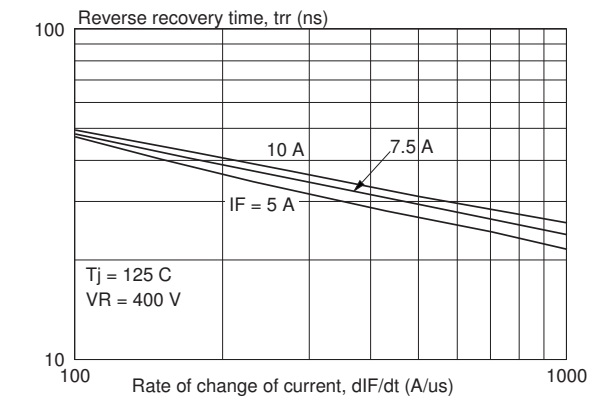


Fig.7. Typical reverse recovery time t_{rr}, per diode as a function of rate of change of current dI_F/dt.

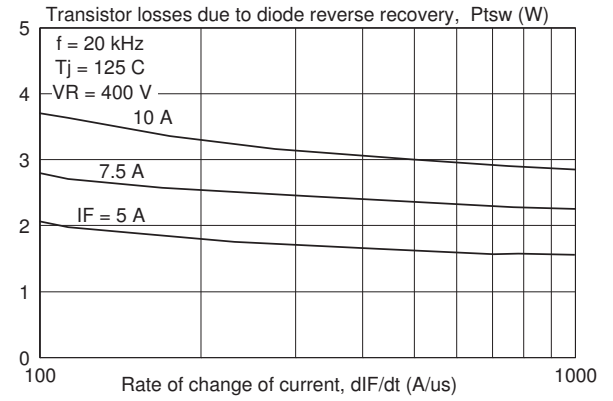


Fig.5. Typical switching losses in transistor due to reverse recovery of diode, as a function of of change of current dI_F/dt.

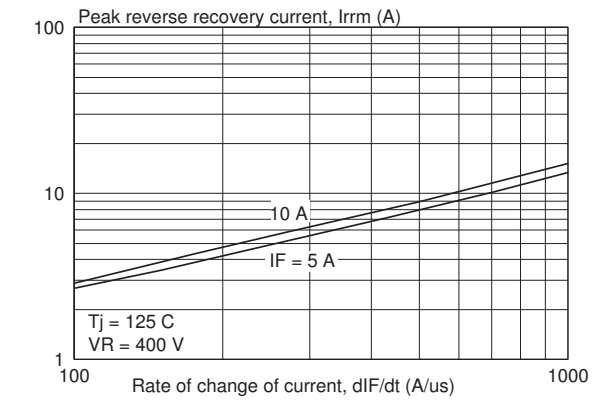


Fig.8. Typical peak reverse recovery current per diode, I_{rrm} as a function of rate of change of current dI_F/dt.

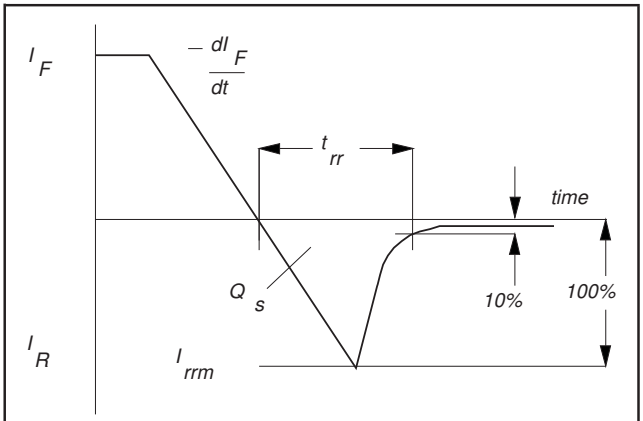


Fig.9. Definition of reverse recovery parameters t_{rr}, I_{rrm}

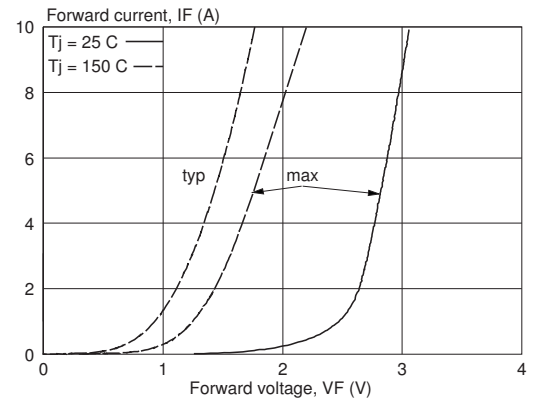


Fig.12. Typical and maximum forward characteristic per diode, $I_F = f(V_F)$; T_j = 25˚C and 150˚C.

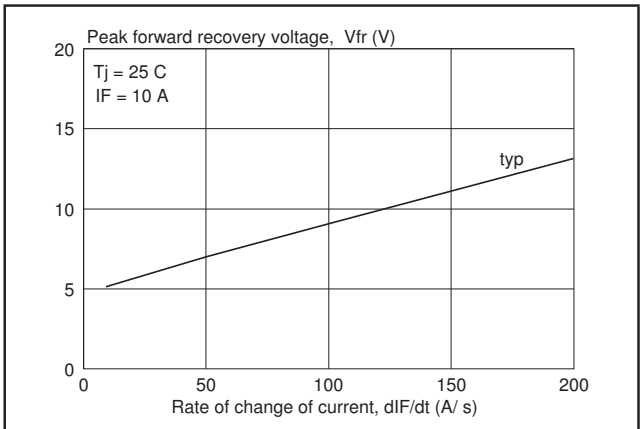


Fig.10. Typical forward recovery voltage per diode, V_{fr} as a function of rate of change of current dI_F/dt.

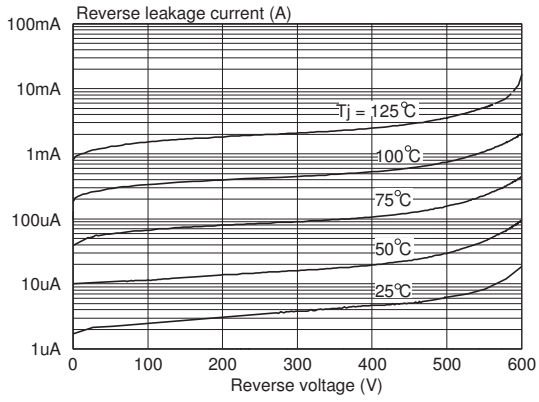


Fig.13. Typical reverse leakage current per diode as a function of reverse voltage. $I_R = f(V_R)$; parameter T_j

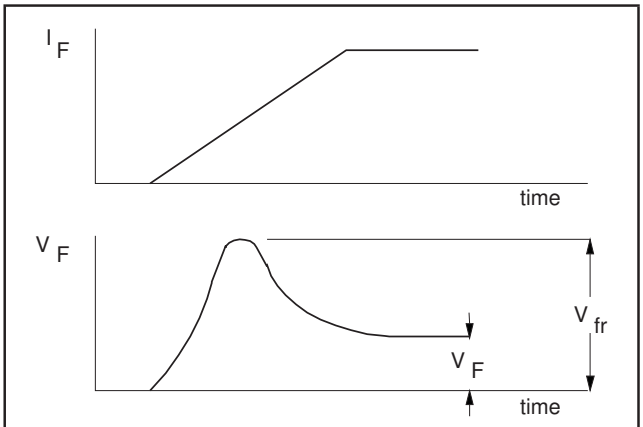


Fig.11. Definition of forward recovery voltage V_{fr}

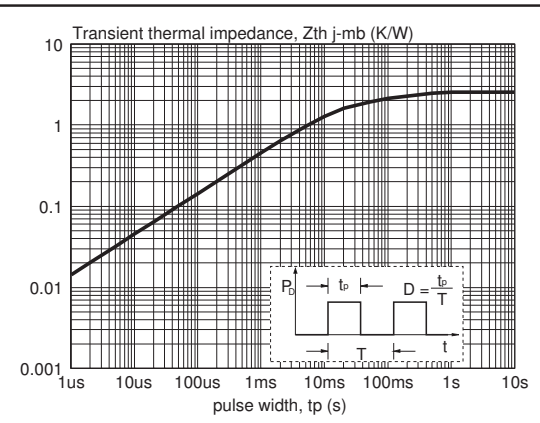


Fig.14. Maximum thermal impedance per diode, $Z_{th\ j\text{-}mb}$ as a function of pulse width.

MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

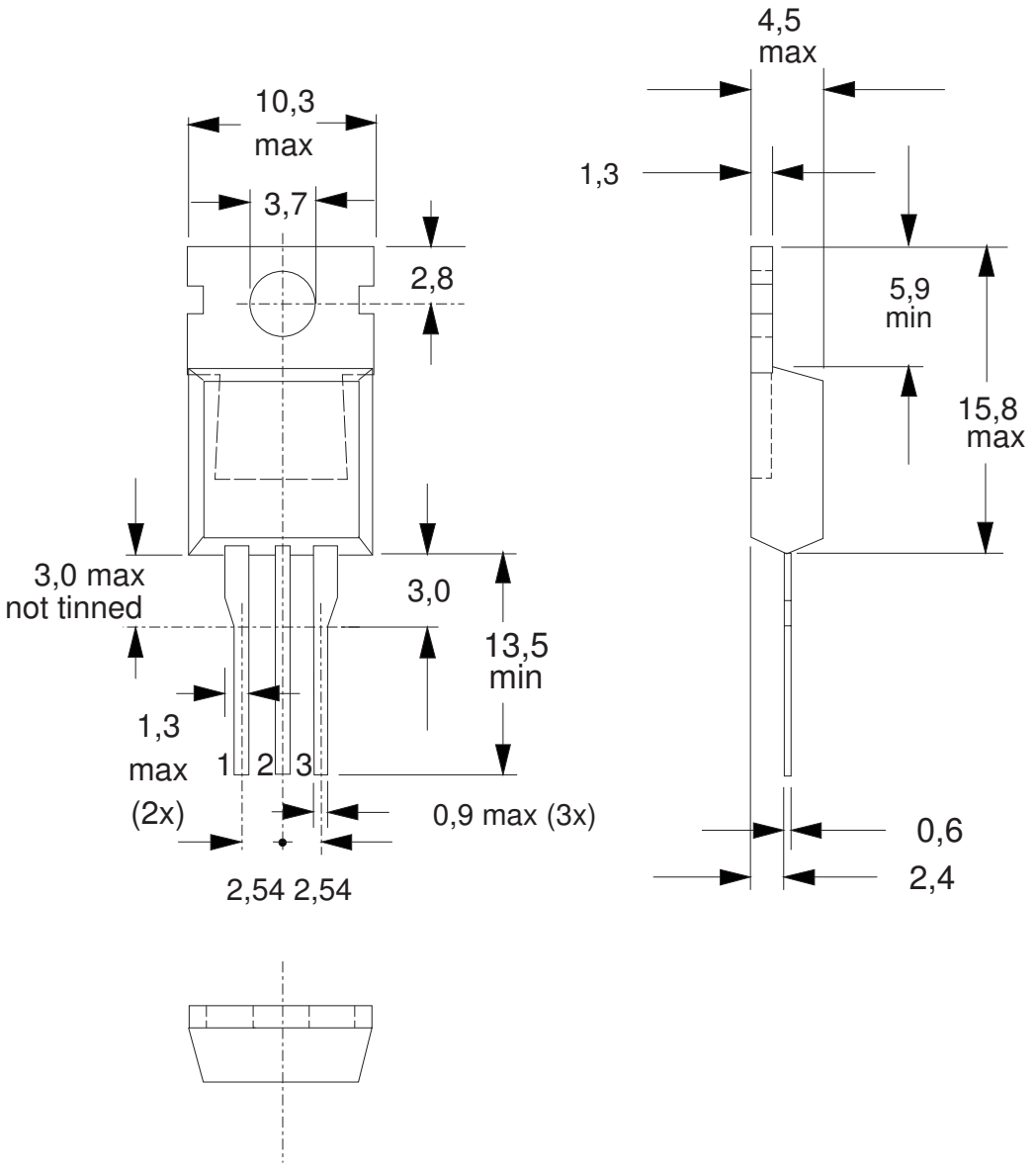


Fig.15. SOT78 (TO220AB); pin 2 connected to mounting base.

Notes
1. Refer to mounting instructions for SOT78 (TO220) envelopes.
2. Epoxy meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Contact information

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